# RGW50TK65D

## 650V 25A Field Stop Trench IGBT

Datasheet

| V <sub>CES</sub>            | 650V |
|-----------------------------|------|
| I <sub>C (100°C)</sub>      | 18A  |
| V <sub>CE(sat) (Typ.)</sub> | 1.5V |
| $P_D$                       | 67W  |

# Outline TO-3PFM

## Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating; RoHS Compliant

## Application

**PFC** 

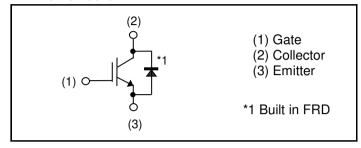
**UPS** 

Welding

Solar Inverter

ΙH

## ●Inner Circuit



●Packaging Specifications

| Packaging Specifications |   |            |  |  |  |
|--------------------------|---|------------|--|--|--|
|                          | Packaging                                       | Tube       |  |  |  |
|                          | Reel Size (mm)                                  | -          |  |  |  |
| Tuno                     | Type Tape Width (mm)  Basic Ordering Unit (pcs) | -          |  |  |  |
| l Type                   |   | 450        |  |  |  |
|                          | Packing Code                                    | C11        |  |  |  |
|                          | Marking   | RGW50TK65D |  |  |  |

## ● **Absolute Maximum Ratings** (at T<sub>C</sub> = 25°C unless otherwise specified)

| Paramet                        | Symbol                   | Value                  | Unit        |    |
|--------------------------------|--------------------------|------------------------|-------------|----|
| Collector - Emitter Voltage    |                          | V <sub>CES</sub>       | 650         | V  |
| Gate - Emitter Voltage         |                          | $V_{GES}$              | ±30         | V  |
| Calleston Cumant               | T <sub>C</sub> = 25°C    | I <sub>C</sub>         | 30          | Α  |
| Collector Current              | T <sub>C</sub> = 100°C   | I <sub>C</sub>         | 18          | Α  |
| Pulsed Collector Current       | Pulsed Collector Current |                        | 100         | Α  |
| Diode Forward Current          | T <sub>C</sub> = 25°C    | l <sub>F</sub>         | 27          | Α  |
|                                | T <sub>C</sub> = 100°C   | l <sub>F</sub>         | 16          | Α  |
| Diode Pulsed Forward Current   | •                        | I <sub>FP</sub> *1 100 |             | Α  |
| Power Dissipation              | T <sub>C</sub> = 25°C    | P <sub>D</sub>         | 67          | W  |
|                                | T <sub>C</sub> = 100°C   | P <sub>D</sub>         | 33          | W  |
| Operating Junction Temperature |                          | T <sub>j</sub>         | -40 to +175 | °C |
| Storage Temperature            |                          | T <sub>stg</sub>       | -55 to +175 | °C |

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

## ●Thermal Resistance

| Doromotor                                | Cumbal            | Values |      |      | Unit  |
|--|-------------------|--------|------|------|-------|
| Parameter                                | Symbol            | Min.   | Тур. | Max. | Offic |
| Thermal Resistance IGBT Junction - Case  | $R_{\theta(j-c)}$ | -      | -    | 2.24 | °C/W  |
| Thermal Resistance Diode Junction - Case | $R_{\theta(j-c)}$ | -      | 1    | 2.79 | °C/W  |

# ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

| Parameter                                 | Symbol               | Conditions  | Values |             |          | Unit  |
|---|----------------------|---|--------|-------------|----------|-------|
| i arameter                                | Symbol               | Conditions  | Min.   | Тур.        | Max.     | Offic |
| Collector - Emitter Breakdown<br>Voltage  | BV <sub>CES</sub>    | $I_{C} = 10 \mu A, V_{GE} = 0 V$  | 650    | ı           | ı        | V     |
| Collector Cut - off Current               | I <sub>CES</sub>     | $V_{CE} = 650V, V_{GE} = 0V$  | ı      | ı           | 10       | μΑ    |
| Gate - Emitter Leakage<br>Current         | I <sub>GES</sub>     | $V_{GE} = \pm 30V$ , $V_{CE} = 0V$  | 1      | 1           | ±200     | nA    |
| Gate - Emitter Threshold<br>Voltage       | $V_{\text{GE(th)}}$  | $V_{CE} = 5V, I_{C} = 16.4mA$   | 5.0    | 6.0         | 7.0      | V     |
| Collector - Emitter Saturation<br>Voltage | V <sub>CE(sat)</sub> | $I_{C} = 25A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$ | -      | 1.5<br>1.85 | 1.9<br>- | ٧     |

# •IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

| Parameter                           | Symbol             | Conditions  | Values |         |      | Unit  |
|-------------------------------------|--------------------|---|--------|---------|------|-------|
| Parameter                           |                    |   | Min.   | Тур.    | Max. | Offic |
| Input Capacitance                   | C <sub>ies</sub>   | $V_{CE} = 30V$ ,  | -      | 2080    | -    |       |
| Output Capacitance                  | C <sub>oes</sub>   | $V_{GE} = 0V$ ,   | -      | 56      | -    | рF    |
| Reverse transfer Capacitance        | C <sub>res</sub>   | f = 1MHz  | -      | 38      | -    |       |
| Total Gate Charge                   | $Q_g$              | $V_{CE} = 400V$ ,   | -      | 73      | -    |       |
| Gate - Emitter Charge               | $Q_ge$             | I <sub>C</sub> = 25A,   | -      | 15      | -    | nC    |
| Gate - Collector Charge             | $Q_{gc}$           | $V_{GE} = 15V$  | -      | 28      | -    |       |
| Turn - on Delay Time                | t <sub>d(on)</sub> |   | -      | 35      | -    |       |
| Rise Time                           | t <sub>r</sub>     | $I_C = 25A, V_{CC} = 400V,$<br>$V_{GF} = 15V, R_G = 10\Omega,$  | -      | 11      | -    | ns    |
| Turn - off Delay Time               | $t_{d(off)}$       | $T_j = 25^{\circ}C$<br>Inductive Load   | 1      | 102     | -    |       |
| Fall Time                           | t <sub>f</sub>     |   | -      | 53      | -    |       |
| Turn - on Switching Loss            | E <sub>on</sub>    | *E <sub>on</sub> include diode<br>reverse recovery  | 1      | 0.39    | -    | mJ    |
| Turn - off Switching Loss           | $E_{off}$          |   | 1      | 0.43    | -    | 1113  |
| Turn - on Delay Time                | $t_{d(on)}$        |   | -      | 34      | -    |       |
| Rise Time                           | t <sub>r</sub>     | $I_C = 25A, V_{CC} = 400V,$<br>$V_{GE} = 15V, R_G = 10\Omega,$  | 1      | 12      | -    | ne    |
| Turn - off Delay Time               | $t_{d(off)}$       | $T_i = 175^{\circ}C$  | -      | 118     | -    | ns    |
| Fall Time                           | t <sub>f</sub>     | Inductive Load  | -      | 78      | -    |       |
| Turn - on Switching Loss            | E <sub>on</sub>    | *E <sub>on</sub> include diode<br>reverse recovery  | -      | 0.41    | -    | mJ    |
| Turn - off Switching Loss           | E <sub>off</sub>   |   | -      | 0.60    | -    | 1113  |
| Reverse Bias Safe Operating<br>Area | RBSOA              | $I_C = 100A$ , $V_{CC} = 520V$ ,<br>$V_P = 650V$ , $V_{GE} = 15V$ ,<br>$R_G = 100\Omega$ , $T_j = 175^{\circ}C$ | FU     | LL SQUA | RE   | -     |

# **•FRD Electrical Characteristics** (at $T_j = 25$ °C unless otherwise specified)

| Parameter                              | Cumbal          | Conditions  | Values |      |      | Unit  |
|--|-----------------|---|--------|------|------|-------|
| Parameter                              | Symbol          |   | Min.   | Тур. | Max. | Offic |
|  |                 | $I_F = 20A$ ,   |        |      |      |       |
| Diode Forward Voltage                  | $V_{F}$         | $T_j = 25^{\circ}C$   | -      | 1.45 | 1.9  | V     |
|  |                 | $T_j = 175$ °C  | -      | 1.55 | -    |       |
| Diode Reverse Recovery<br>Time         | t <sub>rr</sub> |   | -      | 92   | -    | ns    |
| Diode Peak Reverse<br>Recovery Current | I <sub>rr</sub> | $I_F = 20A$ ,<br>$V_{CC} = 400V$ ,<br>$di_F/dt = 200A/\mu s$ ,<br>$T_j = 25^{\circ}C$ | -      | 6.7  | -    | А     |
| Diode Reverse Recovery<br>Charge       | Q <sub>rr</sub> |   | -      | 0.34 | 1    | μC    |
| Diode Reverse Recovery<br>Energy       | E <sub>rr</sub> |   | -      | 14.1 | -    | μJ    |
| Diode Reverse Recovery<br>Time         | t <sub>rr</sub> | $I_F = 20A$ ,<br>$V_{CC} = 400V$ ,<br>$di_F/dt = 200A/\mu s$ ,<br>$T_j = 175$ °C      | -      | 123  | -    | ns    |
| Diode Peak Reverse<br>Recovery Current | I <sub>rr</sub> |   | -      | 7.8  | -    | Α     |
| Diode Reverse Recovery<br>Charge       | Q <sub>rr</sub> |   | _      | 0.59 | -    | μC    |
| Diode Reverse Recovery<br>Energy       | E <sub>rr</sub> |   |        | 30.7 | -    | μJ    |

## Electrical Characteristic Curves

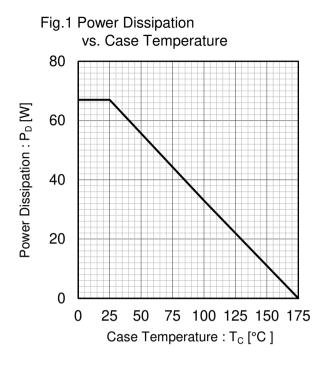


Fig.2 Collector Current vs. Case Temperature

40

20  $T_i \leq 175^{\circ}C$   $T_i \leq 175^{\circ}C$   $T_i \leq 150^{\circ}C$   $T_i \leq 175^{\circ}C$   $T_i \leq 175^$ 

Fig.3 Forward Bias Safe Operating Area

1000

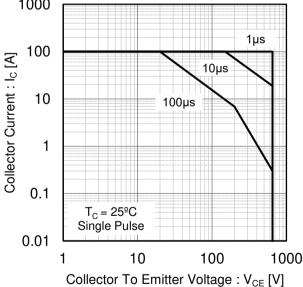
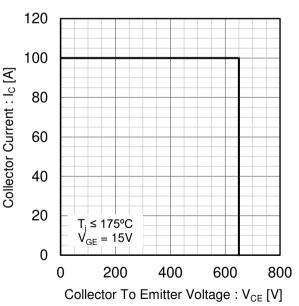


Fig.4 Reverse Bias Safe Operating Area



## ● Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

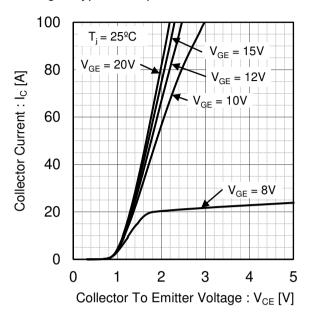


Fig.6 Typical Output Characteristics

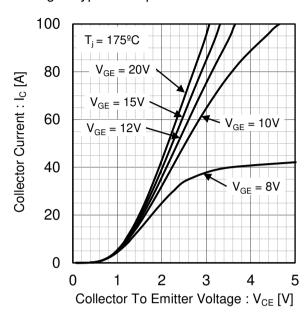


Fig.7 Typical Transfer Characteristics

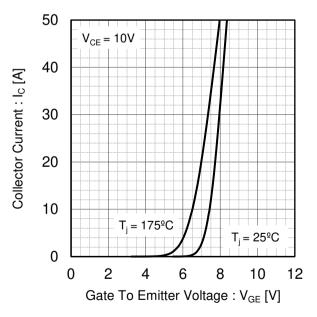
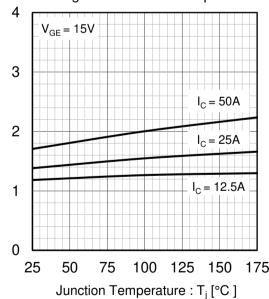


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation

Voltage: V<sub>CE(sat)</sub> [V]



#### Electrical Characteristic Curves

Voltage vs. Gate to Emitter Voltage 20 T<sub>i</sub> = 25<sup>o</sup>C Collector To Emitter Saturation  $I_C = 50A$ 15  $I_C = 25A$ Voltage: V<sub>CE(sat)</sub> [V]  $I_{\rm C} = 12.5 {\rm A}$ 10 5 0 5 10 15 20

Gate To Emitter Voltage: VGE [V]

Fig.9 Typical Collector to Emitter Saturation

Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

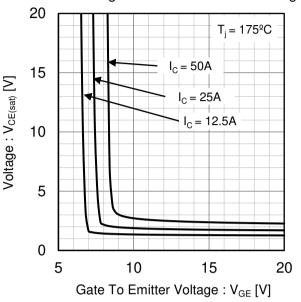


Fig.11 Typical Switching Time vs. Collector Current 1000 Switching Time [ns] 100  $t_{d(on)}$ 10  $V_{CC} = 400V$ ,  $V_{GE} = 15V$ ,  $R_G = 10\Omega$ ,  $T_j = 175^{\circ}C$  Inductive load 1 0 10 20 30 40 50 Collecter Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance 1000  $t_{d(off)}$ Switching Time [ns] 100  $t_{\rm f}$  $t_{d(on)}$ 10  $V_{CC}$  = 400V,  $V_{GE}$  = 15V,  $I_C$  = 25A,  $T_j$  = 175 $^{\circ}$ C Inductive load 1 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Collector To Emitter Saturation

0.01

0

10

## Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

10  $E_{off}$   $E_{off}$   $E_{off}$   $V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10\Omega, T_{j} = 175^{\circ}C$ Inductive load

20

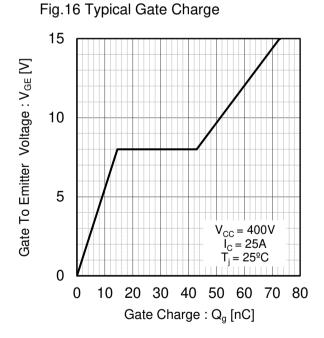
30

Collecter Current : I<sub>C</sub> [A]

50

Fig.14 Typocal Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ] 1  $E_{off}$  $\mathsf{E}_{\mathsf{on}}$ 0.1  $\begin{array}{l} V_{CC}=400V,\ I_{C}=25A,\\ V_{GE}=15V,\ T_{j}=175^{\circ}C\\ Inductive\ load \end{array}$ 0.01 0 10 20 30 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.15 Typical Capacitance vs. Collector to Emitter Voltage 10000  $\mathsf{C}_{\mathsf{ies}}$ 1000 Capacitance [pF] C<sub>oes</sub> 100 10  $C_{res}$ f = 1MHz $V_{GE} = 0V$  $T_i = 25^{\circ}C$ 1 0.01 0.1 1 10 100 Collector To Emitter Voltage: V<sub>CE</sub> [V]



#### Electrical Characteristic Curves

Fig.17 Typical Diode Forward Current vs. Forward Voltage

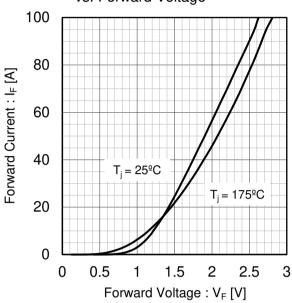


Fig.18 Typical Diode Revese Recovery Time vs. Forward Current

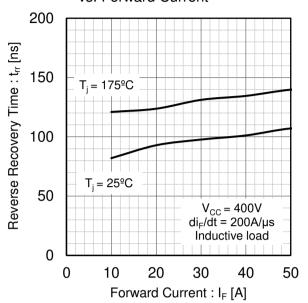


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

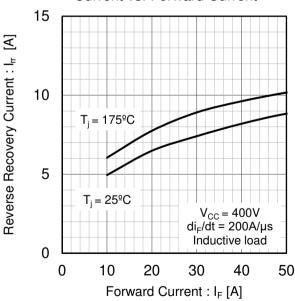
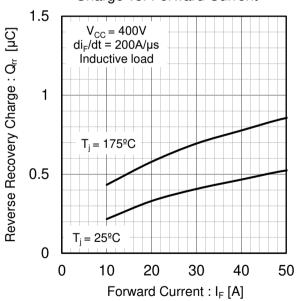


Fig.20 Typical Diode Rrverse Recovery Charge vs. Forward Current



## ● Electrical Characteristic Curves

Fig.21 Typical IGBT Transient Thermal Impedance

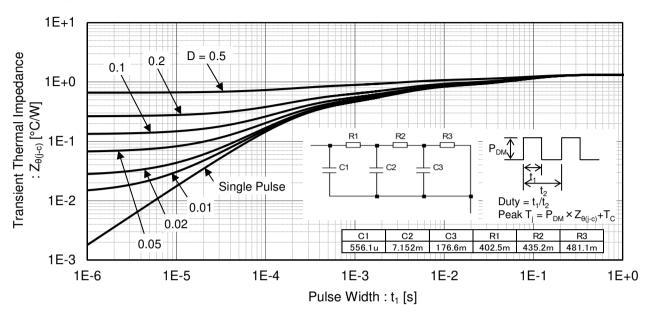
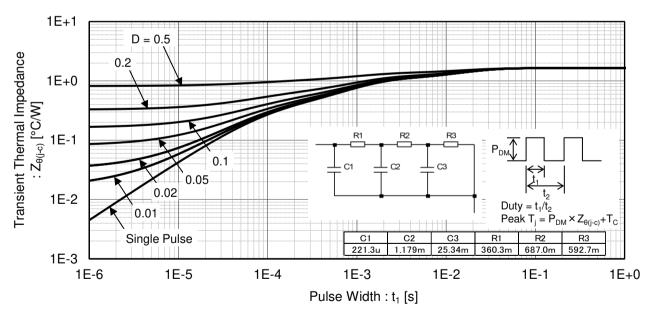


Fig.22 Typical Diode Transient Thermal Impedance



## ●Inductive Load Switching Circuit and Waveform

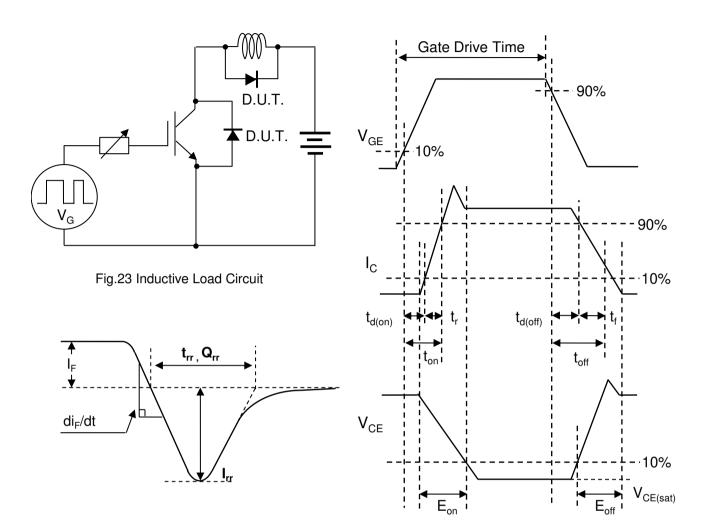


Fig.25 Diode Reverse Recovery Waveform

Fig.24 Inductive Load Waveform

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